1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

2. Features and benefits

- · Logic-level compatible
- Trench12 MOSFET technology
- Efficient switching with soft body-diode recovery
- Automotive qualified to AEC-Q101 at 175 °C
- · Side-wettable flanks for robust solder joints and automatic optical inspection

3. Applications

- 12 V, 24 V and 48 V automotive systems
- · Motors, lamps and solenoid control
- Transmission control
- · LED lighting
- Circuit protection

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	15	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	50	W
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		26.2	38.3	48	mΩ
Dynamic char	acteristics						
Q_{GD}	gate-drain charge	I _D = 5 A; V _{DS} = 40 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		0.4	1.4	3.1	nC
Source-drain	diode						
Q _r	recovered charge	I_S = 15 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 40 V; T_j = 25 °C; Fig. 17		-	7.5	-	nC

^{[1] 15} A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



N-channel 80 V, 48 mOhm logic level MOSFET in LFPAK33

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		D
3	S	source		
4	G	gate		G_(□□□□□)
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1210)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
BUK9M48-80L	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M48-80L	94880L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	80	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	50	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	15	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	15	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	85	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	diode			'	'	
Is	source current	T _{mb} = 25 °C		-	15	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	85	Α
Avalanche ru	ıggedness			'	•	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 4.8 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_{AL} = 110 μs; F_{ig} 4	[2] [3]	-	27.4	mJ

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Symbol	Parameter	Conditions		Min	Max	Unit
I _{AS}	non-repetitive avalanche current	V_{sup} = 80 V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; R_{GS} = 50 Ω ; Fig. 4	[2] [3]	-	4.8	Α

- [1] 15 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

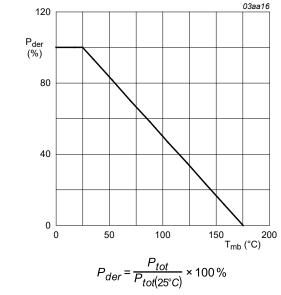
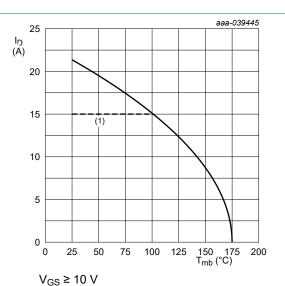


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



(1) 15 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

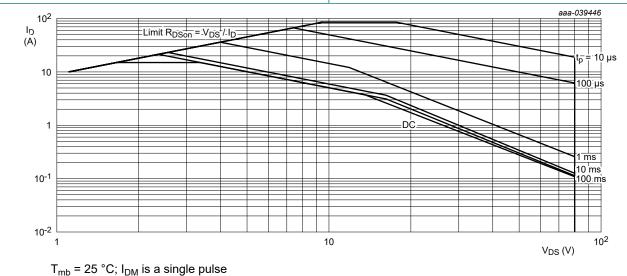
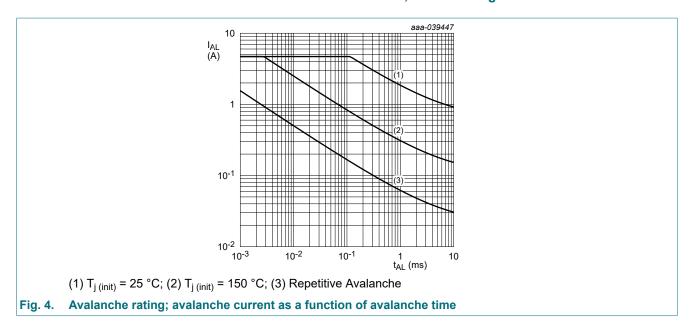


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

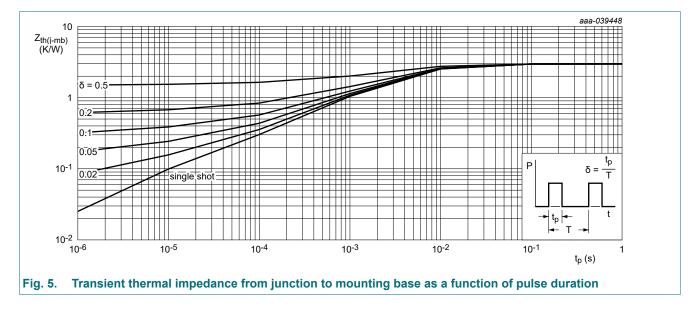
N-channel 80 V, 48 mOhm logic level MOSFET in LFPAK33



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	2.75	2.98	K/W



N-channel 80 V, 48 mOhm logic level MOSFET in LFPAK33

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	80	94	-	V
(=: -)= = =	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _i = -40 °C	73.5	90	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _i = -55 °C	72	89	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 0.03 mA; V _{DS} =V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.05	V
		I _D = 0.03 mA; V _{DS} =V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
		$I_D = 0.03 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 125 °C	-	2	100	μΑ
		V _{DS} = 80 V; V _{GS} = 0 V; T _i = 175 °C	-	16	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	26.2	38.3	48	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 100 °C; Fig. 12	38.5	59	77	mΩ
		V_{GS} = 10 V; I_{D} = 5 A; T_{j} = 125 °C; Fig. 12	42	65	85.3	mΩ
		V_{GS} = 10 V; I_{D} = 5 A; T_{j} = 175 °C; Fig. 12	51	81	110	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$	33.5	53	72	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 105 ^{\circ}\text{C};$ Fig. 12	49	81.5	116	mΩ
		V_{GS} = 4.5 V; I_{D} = 5 A; T_{j} = 125 °C; Fig. 12	54	87	128	mΩ
		V_{GS} = 4.5 V; I_{D} = 5 A; T_{j} = 175 °C; Fig. 12	65.3	108	165	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.9	1.8	3.6	Ω
Dynamic ch	naracteristics			'		
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 40 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	2.8	5.7	8.6	nC
		I _D = 5 A; V _{DS} = 40 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	5.5	10.9	16.5	nC
Q _{GS}	gate-source charge	I _D = 5 A; V _{DS} = 40 V; V _{GS} = 5 V;	1.3	2.2	3	nC
Q_{GD}	gate-drain charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	0.4	1.4	3.1	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 5 A; V _{DS} = 40 V; T _j = 25 °C; <u>Fig. 13;</u> <u>Fig. 14</u>	-	3	-	V
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	418	697	975	pF
Coss	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	116	193	308	pF
C _{rss}	reverse transfer capacitance		7.8	19	31	pF

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 8 \Omega; V_{GS} = 5 \text{ V};$		-	6.4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$		-	4.9	-	ns
$t_{d(off)}$	turn-off delay time			-	8.3	-	ns
t _f	fall time	1		-	5	-	ns
Source-dra	in diode				•	•	
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.93	1	V
t _{rr}	reverse recovery time	$I_S = 15 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;		-	17.5	-	ns
Q _r	recovered charge	V _{DS} = 40 V; T _j = 25 °C; <u>Fig. 17</u>		-	7.5	-	nC

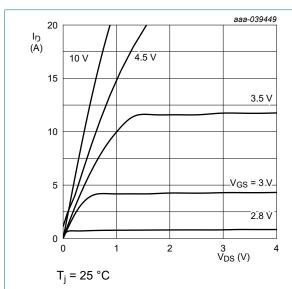


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

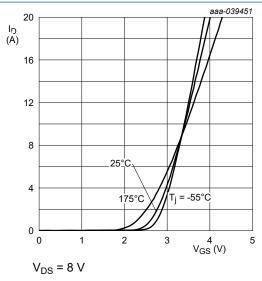


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

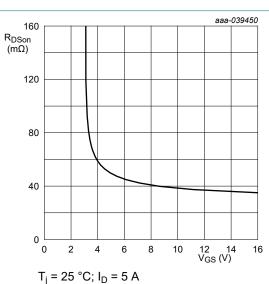
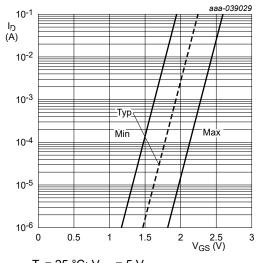


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

Fig. 9. Sub-threshold drain current as a function of gate-source voltage

N-channel 80 V, 48 mOhm logic level MOSFET in LFPAK33

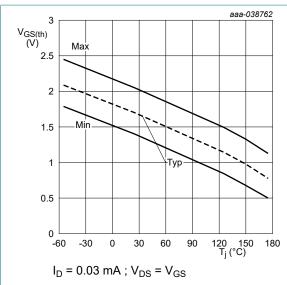


Fig. 10. Gate-source threshold voltage as a function of junction temperature

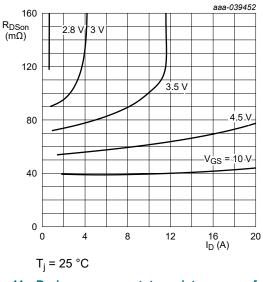


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

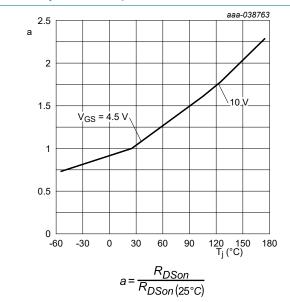


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

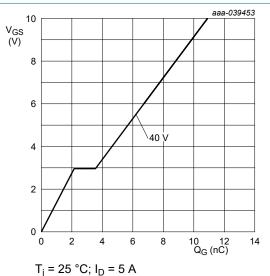


Fig. 13. Gate-source voltage as a function of gate charge; typical values

N-channel 80 V, 48 mOhm logic level MOSFET in LFPAK33

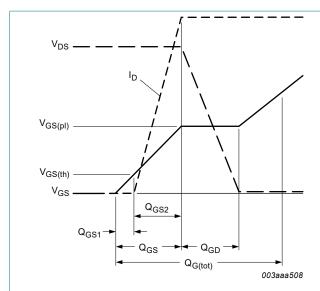


Fig. 14. Gate charge waveform definitions

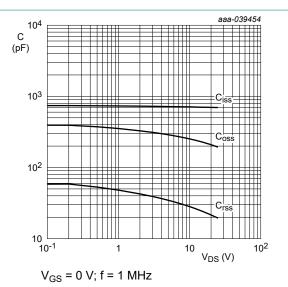


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

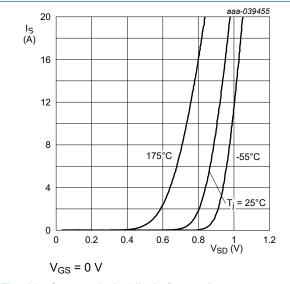


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

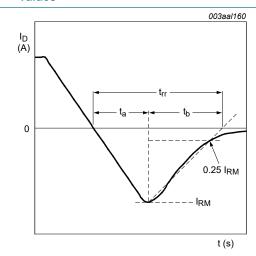


Fig. 17. Reverse recovery timing definition

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11. Package outline

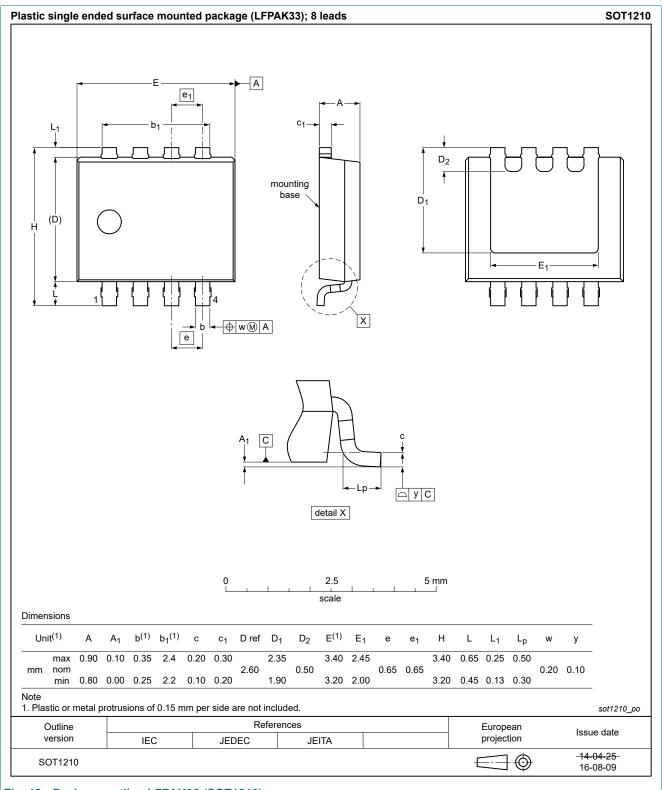
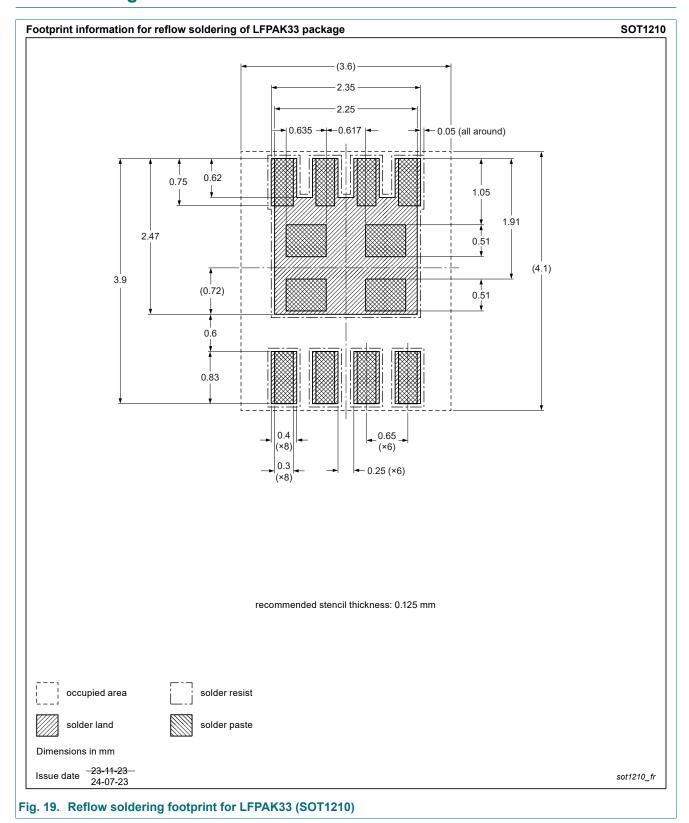


Fig. 18. Package outline LFPAK33 (SOT1210)

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12. Soldering



DUIZOMAO OOL

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13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BUK9M48-80L

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